

P-Channel 80 V (D-S) MOSFET

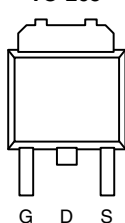
PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^b	Q_g (Typ)
- 80	0.0112 at $V_{GS} = - 10$ V	- 110	85 nC
	0.0145 at $V_{GS} = - 4.5$ V	- 109	

FEATURES

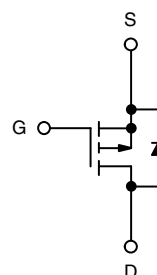
- TrenchFET[®] Power MOSFET
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912


RoHS
COMPLIANT

TO-263


Top View

Drain Connected to Tab

Ordering Information: SUM110P08-11L-E3 (Lead (Pb)-free)


P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 80	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C - 110 ^a	A
		$T_C = 125$ °C - 71	
		$T_A = 25$ °C - 23.5 ^{b, c}	
		$T_A = 125$ °C - 13.6 ^{b, c}	
Pulsed Drain Current	I_{DM}	- 120	
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C - 110	
		$T_A = 25$ °C - 9 ^{b, c}	
Avalanche Current	I_{AS}	- 75	mJ
Single-Pulse Avalanche Energy	E_{AS}	281	
Maximum Power Dissipation	P_D	$T_C = 25$ °C 375	W
		$T_C = 125$ °C 125	
		$T_A = 25$ °C 13.6 ^{b, c}	
		$T_A = 125$ °C 4.5 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	8	11	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	0.33	0.4	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under steady state conditions is 40 °C/W.

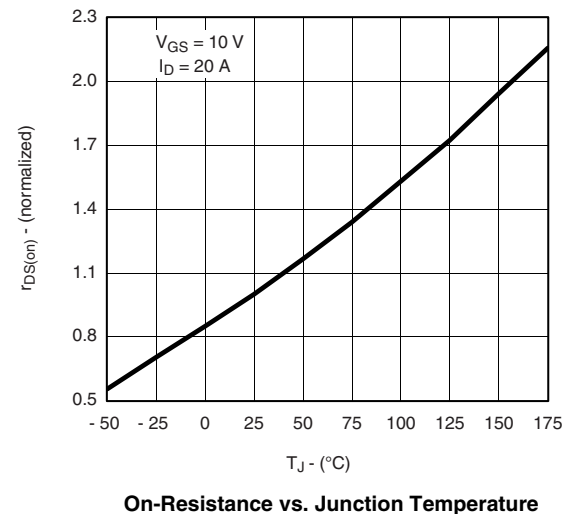
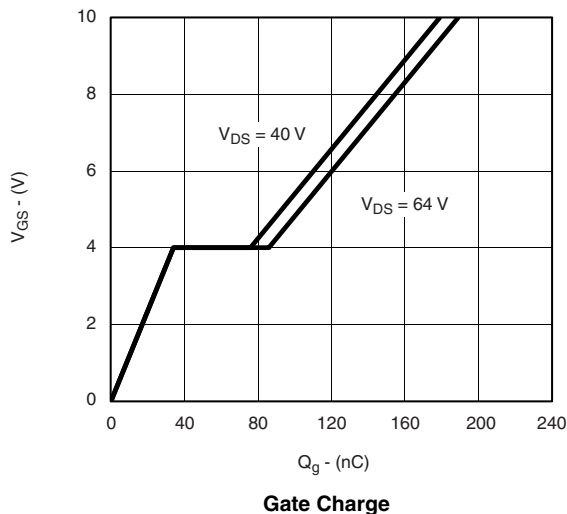
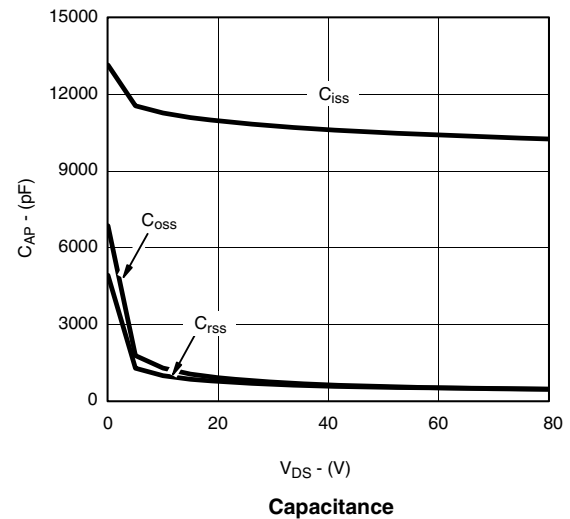
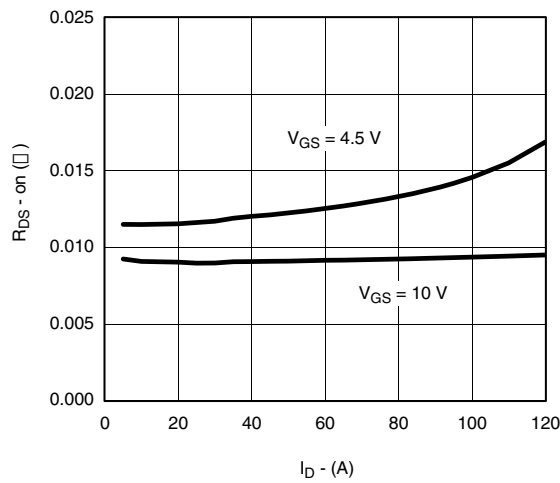
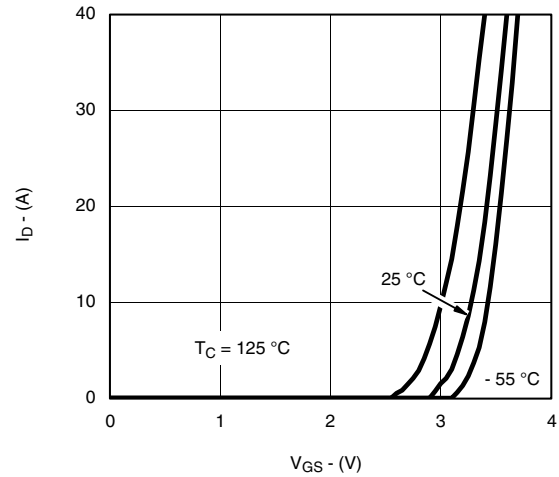
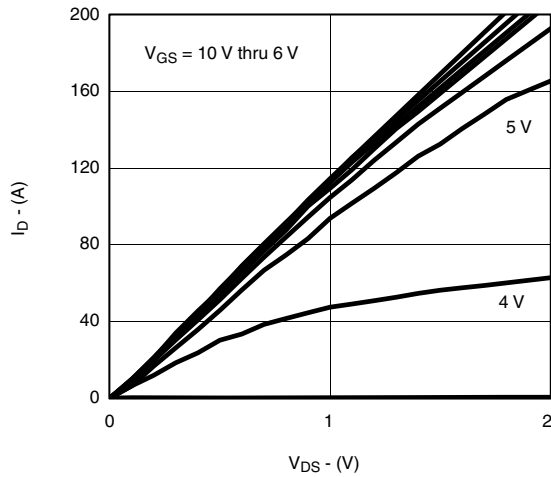
SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 80			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 1 μA		- 85		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.5			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 80 V, V _{GS} = 0 V			- 1	μA	
		V _{DS} = - 80 V, V _{GS} = 0 V, T _J = 175 °C			- 500		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = - 10 V	- 120			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 20 A		0.0093	0.0112	Ω	
		V _{GS} = - 4.5 V, I _D = - 15 A		0.0120	0.0145		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 20 A		85		S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = - 40 V, V _{GS} = 0 V, f = 1 MHz		10850		pF	
Output Capacitance	C _{oss}			800			
Reverse Transfer Capacitance	C _{rss}			700			
Total Gate Charge	Q _g	V _{DS} = - 40 V, V _{GS} = - 10 V, I _D = - 110 A		180	270	nC	
Gate-Source Charge	Q _{gs}	V _{DS} = - 40 V, V _{GS} = - 4.5 V, I _D = - 110 A		85	130		
Gate-Drain Charge	Q _{gd}			35			
Gate Resistance	R _g			42			
Turn-On Delay Time	t _{d(on)}	f = 1 MHz		3.6		Ω	
Rise Time	t _r		V _{DD} = - 40 V, R _L = 0.36 Ω I _D ≅ - 110 A, V _{GEN} = - 10 V, R _g = 1 Ω		20	30	ns
Turn-Off Delay Time	t _{d(off)}				330	500	
Fall Time	t _f				135	205	
				550	825		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 110	A	
Pulse Diode Forward Current ^a	I _{SM}				- 120		
Body Diode Voltage	V _{SD}	I _S = - 20 A		- 0.8	- 1.5	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 20 A, di/dt = 100 A/μs, T _J = 25 °C		65	100	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			135	205	nC	
Reverse Recovery Fall Time	t _a			43		ns	
Reverse Recovery Rise Time	t _b			22			

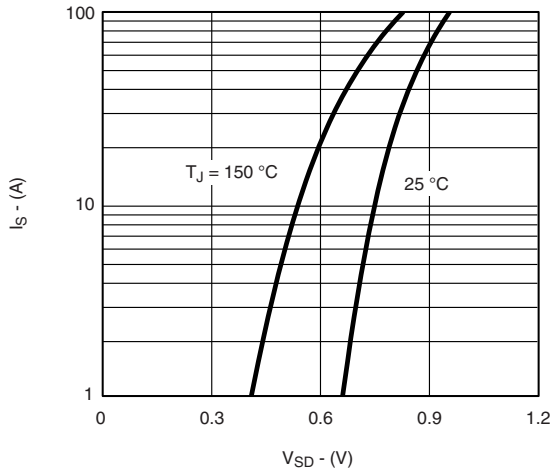
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

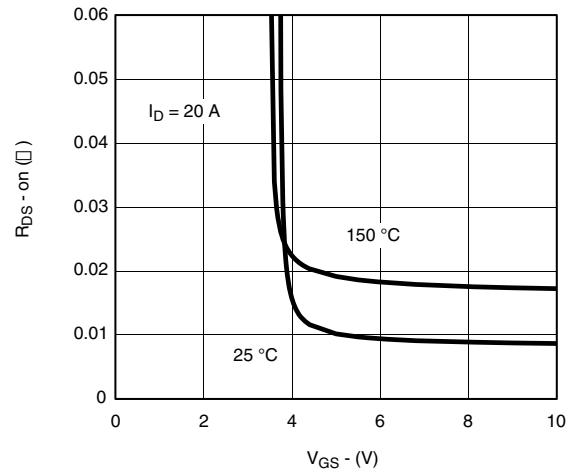
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

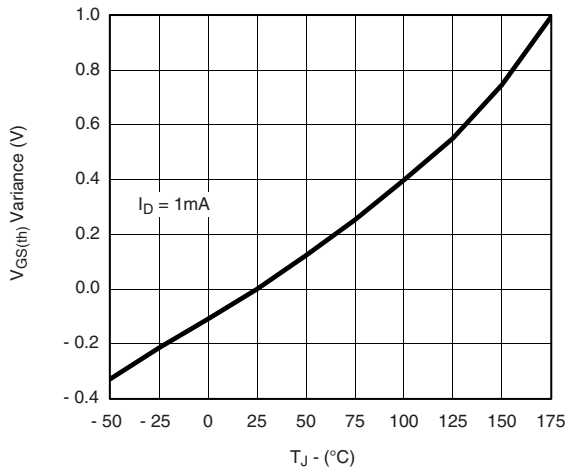
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

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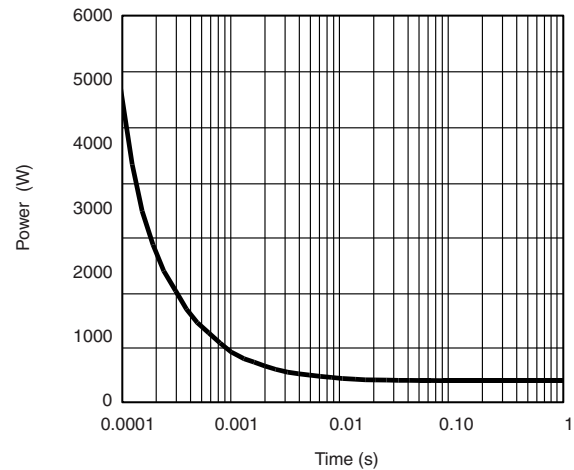
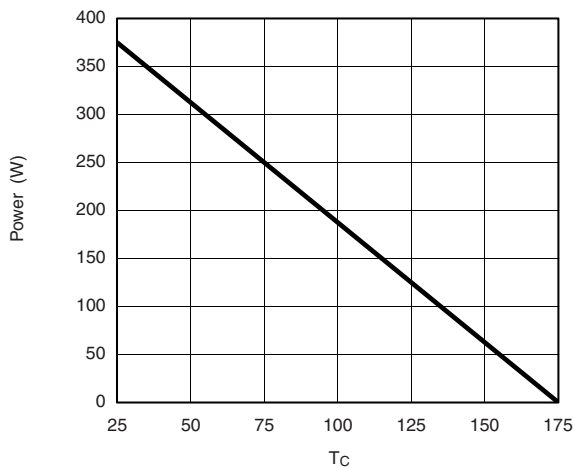
Source-Drain Diode Forward Voltage



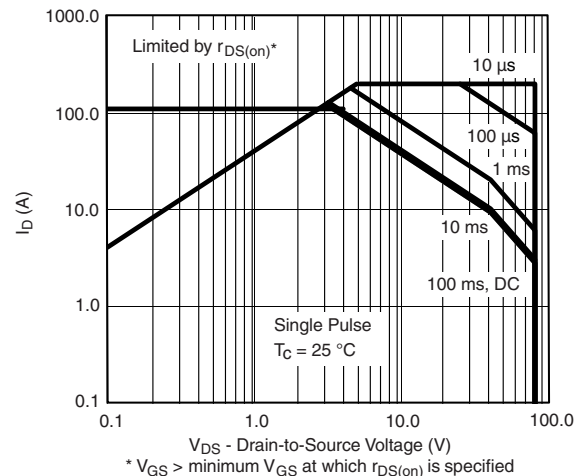
On-Resistance vs. Gate-to-Source Voltage



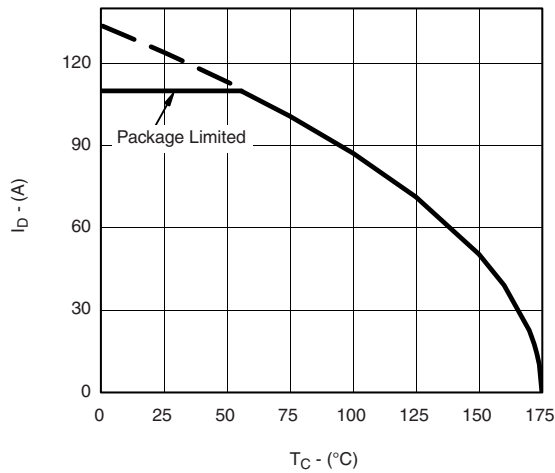
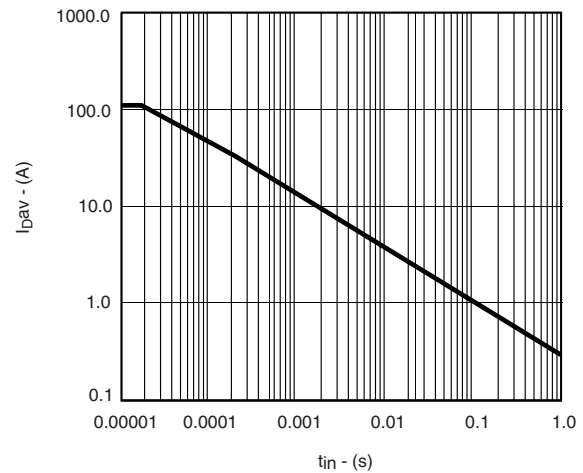
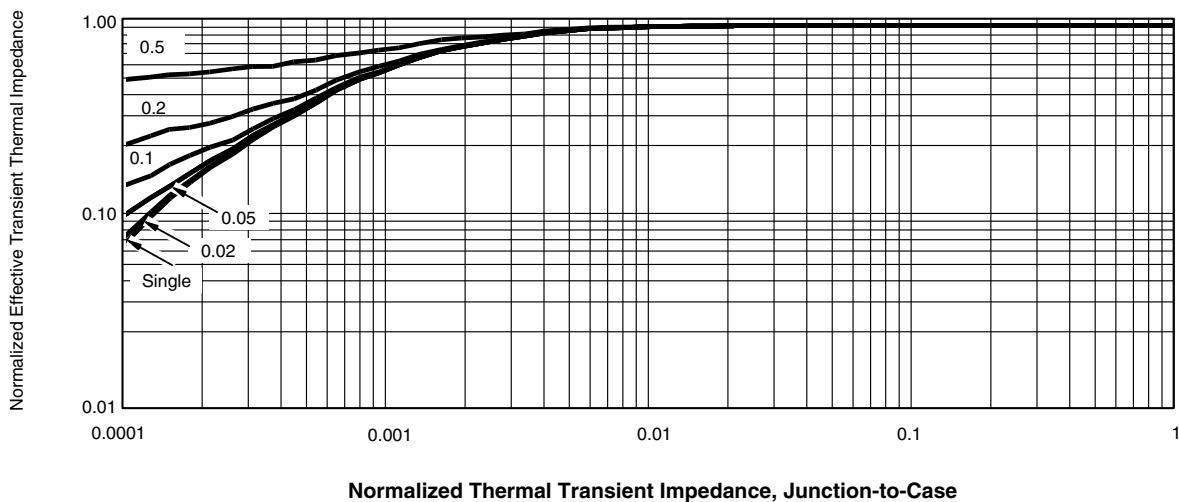
Threshold Voltage

Single Pulse Power, Junction-to-Case ($T_C = 25^\circ\text{C}$)

Power Derating, Junction-to-Case



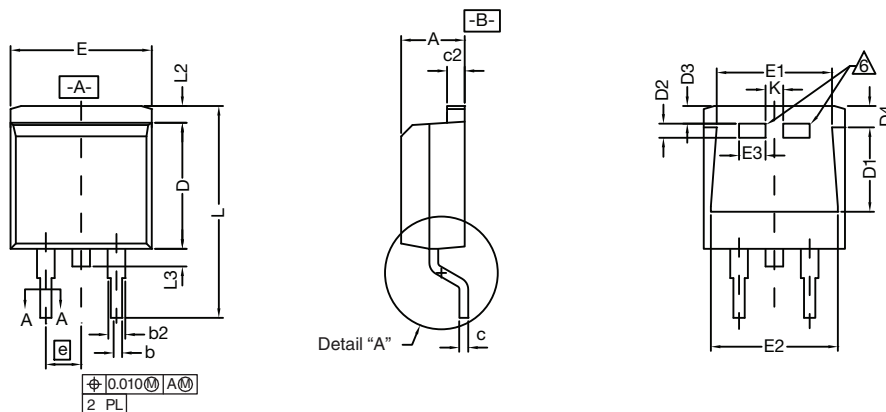
Safe Operating Area

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Max. Avalanche and Drain Current vs. Case Temperature****Avalanche Current vs. Time**

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TO-263 (D²PAK): 3-LEAD

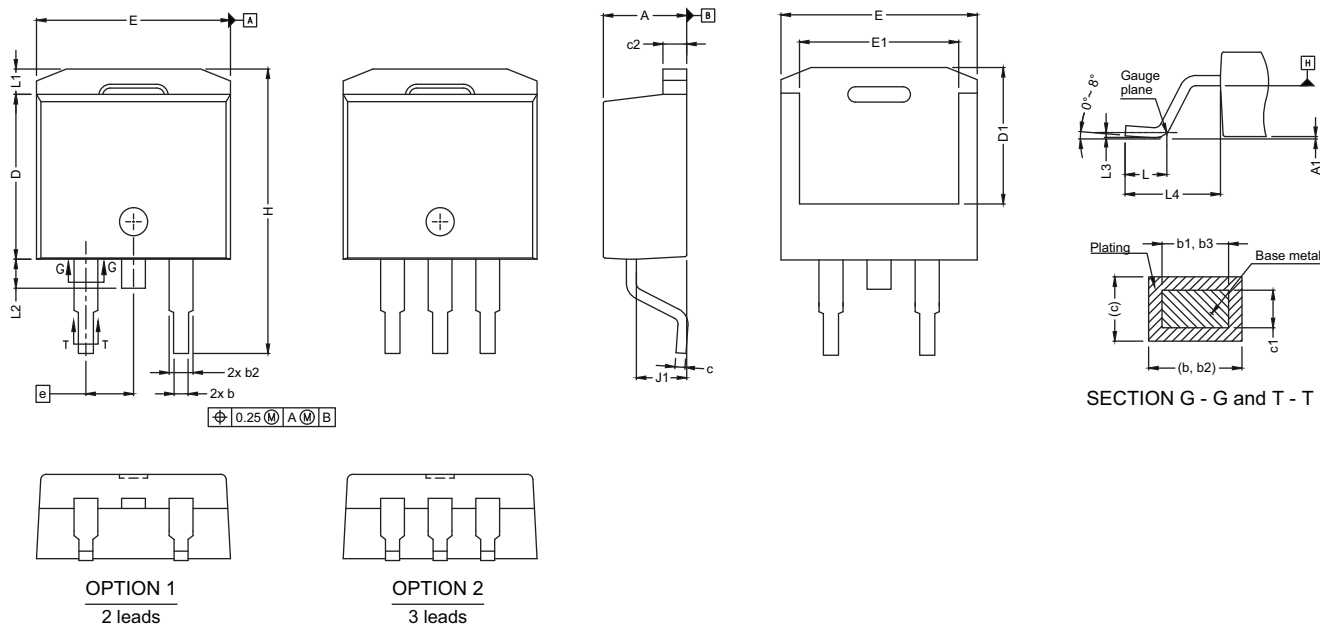
VERSION 1: FACILITY CODE = T



DIM.		INCHES		MILLIMETERS	
		MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.

VERSION 2: FACILITY CODE = N

DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
c	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
e	2.54 BSC	
H	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 typ.	
L4	4.78	5.28
J1	2.56	2.96

ECN: S24-1080-Rev. L, 28-Oct-2024

DWG: 5843

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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